NSN 5961-01-289-8544

Semiconductor Device Set - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-289-8544 **Inclosure Material:** Metal all transistor **Overall Length:** 1.187 inches all transistor Overall Diameter: 0.610 inches all transistor **End Application:** F-15 acft **Mounting Facility Quantity:** 1 all transistor **Internal Configuration:** Junction contact all transistor **Internal Junction Configuration:** Npn all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Threaded stud all transistor Field Force Effect Type: Electrostatic charge **Overall Width Across Flats:** 0.687 inches all transistor **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 120.0 breakdown voltage, collector-to-base, emitter open all transistor and 90.0 breakdown voltage, collector-to-emitter, base open all transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor **Current Rating Per Characteristic:** 10.00 milliamperes zero-gate-voltage source current preset all transistor and 10.00 milliamperes zero-gate-voltage source current major all transistor **Test Data Document:** 13973-862182 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 tab, solder lug all transistor Shelf Life: N/a **Unit Of Measure:**

Fiig:

No

Demilitarization: